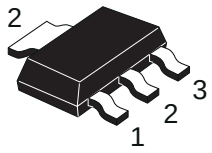
BCP55
BCP56

SMALL SIGNAL NPN TRANSISTORS

PRELIMINARY DATA

Type	Marking
BCP55	BCP55
BCP56	BCP56

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTORS
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPES ARE BCP52 AND BCP53 RESPECTIVELY

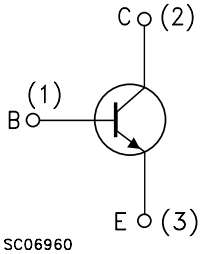


SOT-223

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BCP55	BCP56	
V_{CBO}	Collector-Base Voltage (I_E = 0)	60	100	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	60	80	V
V_{CER}	Collector-Emitter Voltage (R_{BE} = 1KΩ)	60	100	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	5		V
I_C	Collector Current	1		A
I_{CM}	Collector Peak Current (t_p < 5 ms)	1.5		A
I_B	Base Current	0.1		A
I_{BM}	Base Peak Current (t_p < ms)	0.2		A
P_{tot}	Total Dissipation at T_c = 25 °C	2		W
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

THERMAL DATA

$R_{thj\text{-}amb}$ •	Thermal Resistance Junction-Ambient	Max	62.5	$^oC/W$

• Device mounted on a PCB area of 1 cm^2

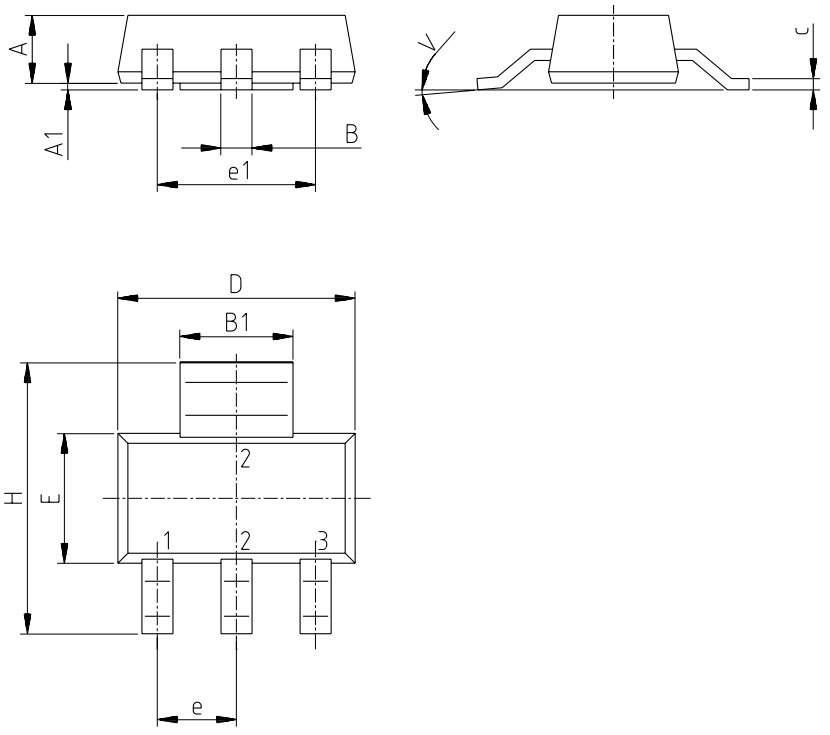
ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = 30 V V_{CB} = 30 V T_C = 125 ^oC			100 10	nA µA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I_E = 0)	I_C = 100 µA for **BCP55** for **BCP56**	 60 100			 V V
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage (I_B = 0)	I_C = 20 mA for **BCP55** for **BCP56**	 60 80			 V V
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage (R_{BE} = 1 KΩ)	I_C = 100 µA for **BCP55** for **BCP56**	 60 100			 V V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_C = 10 µA	5			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 500 mA I_B = 50 mA			0.5	V
$V_{BE(on)}$*	Base-Emitter On Voltage	I_C = 500 mA V_{CE} = 2 V			1	V
h_{FE}*	DC Current Gain	I_C = 5 mA V_{CE} = 2 V I_C = 150 mA V_{CE} = 2 V for Gr. 16 I_C = 500 mA V_{CE} = 2 V	25 100 25		250	
f_T	Transition Frequency	I_C = 10 mA V_{CE} = 5 V f = 35 MHz		50		MHz

∗ Pulsed: Pulse duration = 300 µs, duty cycle ≤ 1.5 %

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10^o			10^o
A1		0.02				



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